Dual-gate MOS-FET | BF1100WR

FEATURES

- Specially designed for use at 9 to 12 V supply voltage
- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Superior cross-modulation performance during AGC.

APPLICATIONS

- VHF and UHF applications such as television tuners and professional communications equipment.

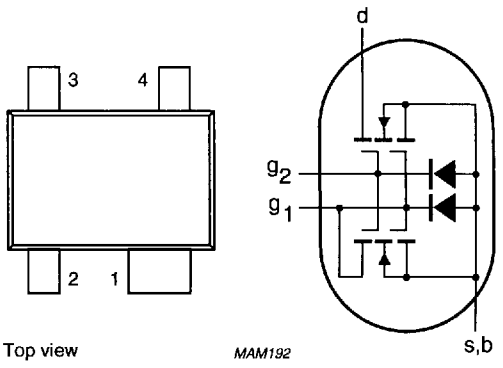
DESCRIPTION

Enhancement type field-effect transistor in a plastic microminiature SOT343R package. The transistor consists of an amplifier MOS-FET with source and substrate interconnected and an internal bias circuit to ensure good cross-modulation performance during AGC.

CAUTION
The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g_2	gate 2
4	g_1	gate 1



Marking code: MF.

Fig.1 Simplified outline (SOT343R) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	14	V
I_D	drain current		–	–	30	mA
P_{tot}	total power dissipation		–	–	280	mW
T_j	operating junction temperature		–	–	150	°C
$\|y_{fs}\|$	forward transfer admittance		24	28	33	mS
C_{ig1-s}	input capacitance at gate 1		–	2.2	2.6	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz	–	25	35	fF
F	noise figure	f = 800 MHz	–	2	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	14	V
I_D	drain current		–	30	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	see Fig.2; up to T_{amb} = 50 °C; note 1	–	280	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	+150	°C

Note

1. Device mounted on a printed-circuit board.

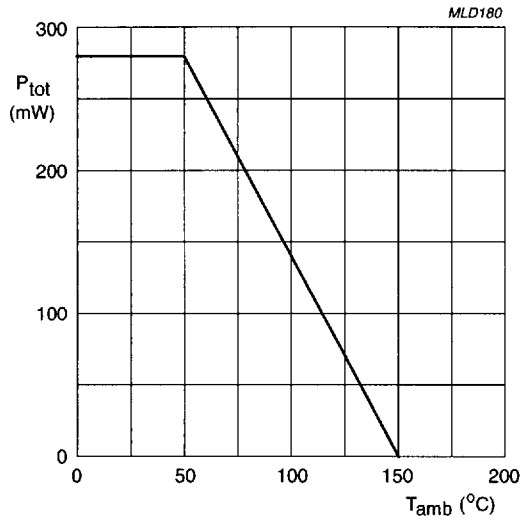


Fig.2 Power derating curve.

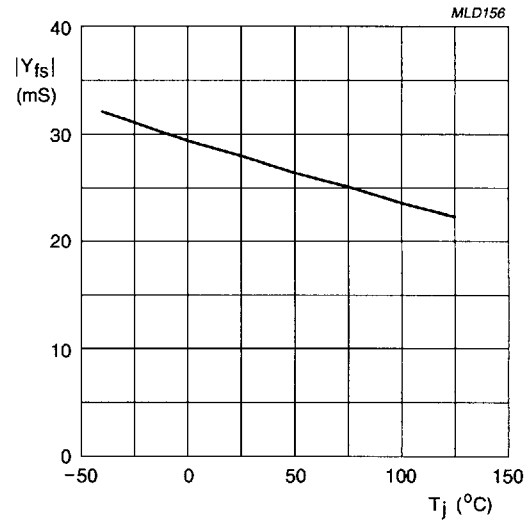


Fig.3 Forward transfer admittance as a function of junction temperature; typical values.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	350	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	T_s = 91 °C; note 2	210	K/W

Notes

1. Device mounted on a printed-circuit board.
2. T_s is the temperature at the soldering point of the source lead.

STATIC CHARACTERISTICS

T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)G1\text{-}SS}$	gate 1-source breakdown voltage	$V_{G2\text{-}S} = V_{DS} = 0$; $I_{G1\text{-}S}$ = 1 mA	13.2	20	V
$V_{(BR)G2\text{-}SS}$	gate 2-source breakdown voltage	$V_{G1\text{-}S} = V_{DS} = 0$; $I_{G2\text{-}S}$ = 1 mA	13.2	20	V
$V_{(F)S\text{-}G1}$	forward source-gate 1 voltage	$V_{G2\text{-}S} = V_{DS} = 0$; $I_{S\text{-}G1}$ = 10 mA	0.5	1.5	V
$V_{(F)S\text{-}G2}$	forward source-gate 2 voltage	$V_{G1\text{-}S} = V_{DS} = 0$; $I_{S\text{-}G2}$ = 10 mA	0.5	1.5	V
$V_{G1\text{-}S(th)}$	gate 1-source threshold voltage	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 9 V; I_D = 20 µA	0.3	1	V
		$V_{G2\text{-}S}$ = 4 V; V_{DS} = 12 V; I_D = 20 µA	0.3	1	V
$V_{G2\text{-}S(th)}$	gate 2-source threshold voltage	$V_{G1\text{-}S}$ = 4 V; V_{DS} = 9 V; I_D = 20 µA	0.3	1.2	V
		$V_{G1\text{-}S}$ = 4 V; V_{DS} = 12 V; I_D = 20 µA	0.3	1.2	V
I_{DSX}	drain-source current	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 9 V; R_{G1} = 180 kΩ; note 1	8	13	mA
		$V_{G2\text{-}S}$ = 4 V; V_{DS} = 12 V; R_{G1} = 250 kΩ; note 2	8	13	mA
$I_{G1\text{-}SS}$	gate 1 cut-off current	$V_{G2\text{-}S} = V_{DS} = 0$; $V_{G1\text{-}S}$ = 12 V	–	50	nA
$I_{G2\text{-}SS}$	gate 2 cut-off current	$V_{G1\text{-}S} = V_{DS} = 0$; $V_{G2\text{-}S}$ = 12 V	–	50	nA

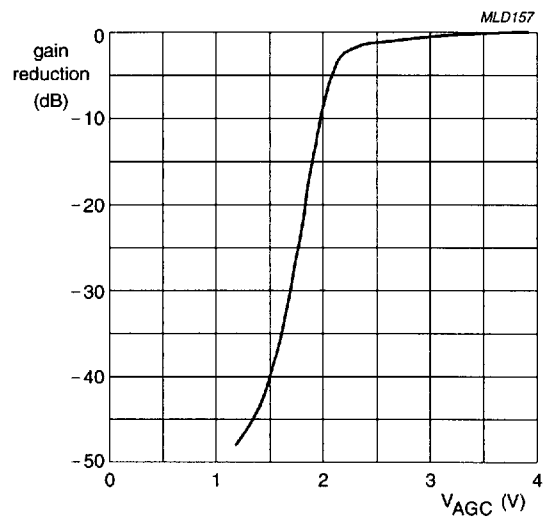
Notes

1. R_{G1} connects gate 1 to V_{GG} = 9 V; see Fig.26.
2. R_{G1} connects gate 1 to V_{GG} = 12 V; see Fig.26.

DYNAMIC CHARACTERISTICS

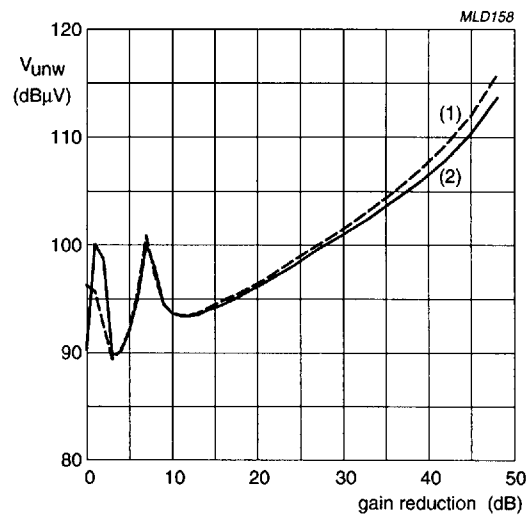
Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; I_D = 10 mA; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\|y_{fs}\|$	forward transfer admittance	pulsed; T_j = 25 °C				
		V_{DS} = 9 V	24	28	33	mS
		V_{DS} = 12 V	24	28	33	mS
C_{ig1-s}	input capacitance at gate 1	f = 1 MHz				
		V_{DS} = 9 V	–	2.2	2.6	pF
		V_{DS} = 12 V	–	2.2	2.6	pF
C_{ig2-s}	input capacitance at gate 2	f = 1 MHz				
		V_{DS} = 9 V	–	1.6	–	pF
		V_{DS} = 12 V	–	1.4	–	pF
C_{os}	drain-source capacitance	f = 1 MHz				
		V_{DS} = 9 V	–	1.4	1.8	pF
		V_{DS} = 12 V	–	1.1	1.5	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz				
		V_{DS} = 9 V	–	25	35	fF
		V_{DS} = 12 V	–	25	35	fF
F	noise figure	f = 800 MHz; $G_S = G_{Sopt}$; $B_S = B_{Sopt}$				
		V_{DS} = 9 V	–	2	2.8	dB
		V_{DS} = 12 V	–	2	2.8	dB



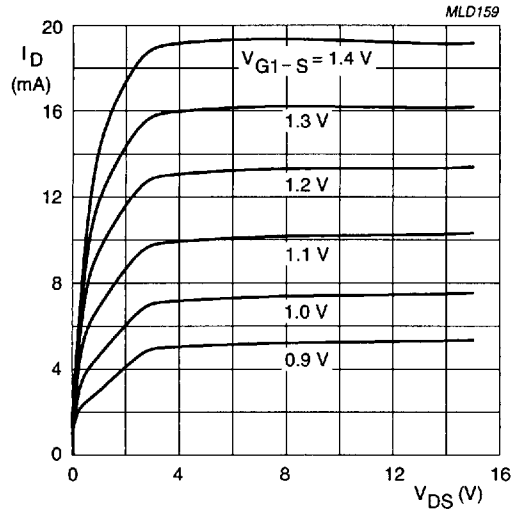
f = 50 MHz.
T_j = 25 °C.

Fig.4 Gain reduction as a function of the AGC voltage; typical values.



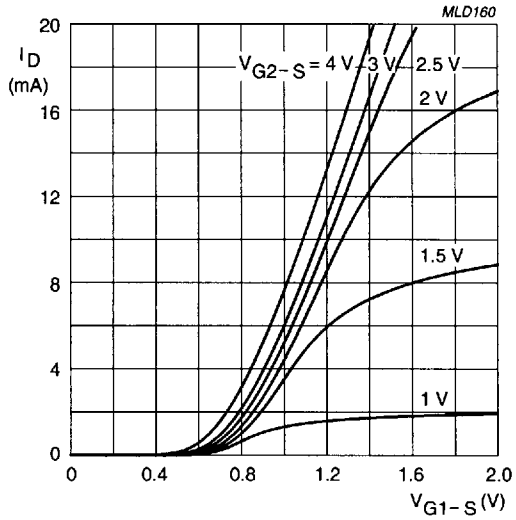
(1) R_G = 250 kΩ to V_{GG} = 12 V.
(2) R_G = 180 kΩ to V_{GG} = 9 V.
f_w = 50 MHz; f_{unw} = 60 MHz; T_{amb} = 25 °C.

Fig.5 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; see Fig.26.



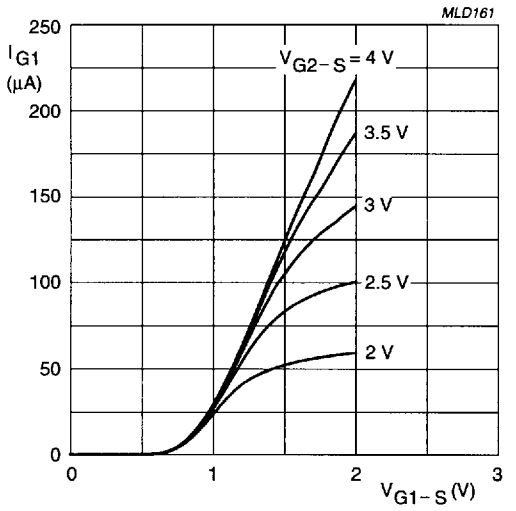
V_{G2-S} = 4 V.
T_j = 25 °C.

Fig.6 Output characteristics; typical values.



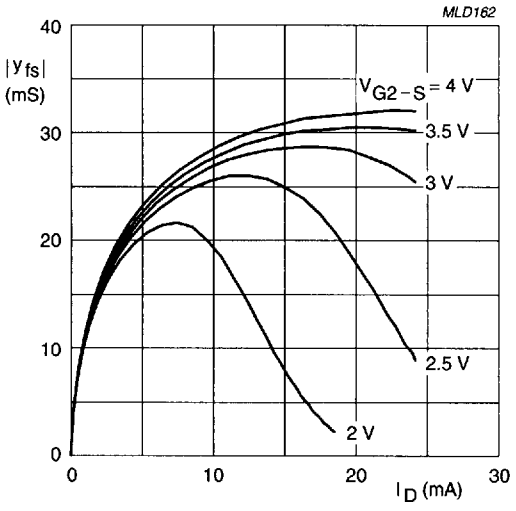
V_{DS} = 9 to 12 V.
T_j = 25 °C.

Fig.7 Transfer characteristics; typical values.



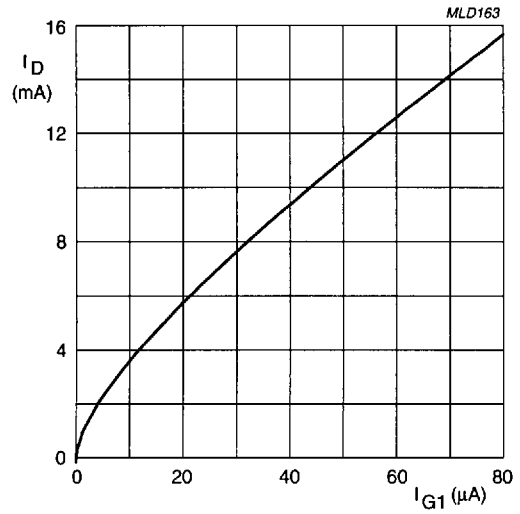
V_{DS} = 9 to 12 V.
T_j = 25 °C.

Fig.8 Gate 1 current as a function of gate 1 voltage; typical values.



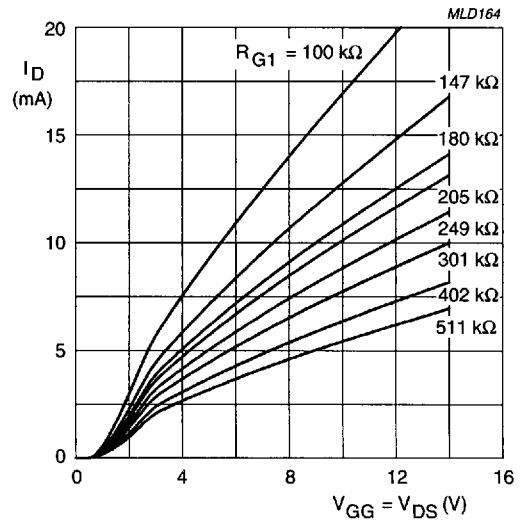
V_{DS} = 9 to 12 V.
T_j = 25 °C.

Fig.9 Forward transfer admittance as a function of drain current; typical values.



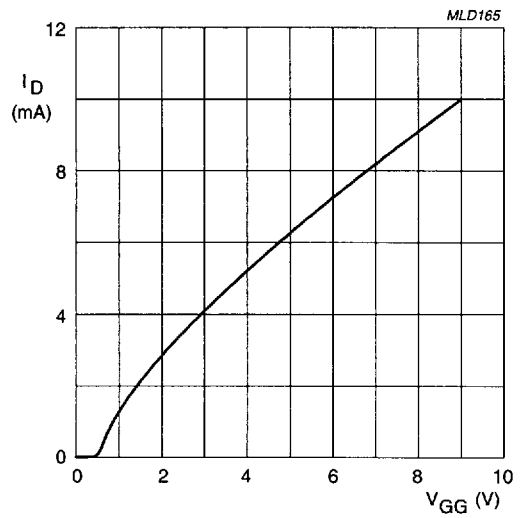
V_{DS} = 9 to 12 V.
$V_{G2\text{-}S}$ = 4 V.
T_j = 25 °C.

Fig.10 Drain current as a function of gate 1 current; typical values.



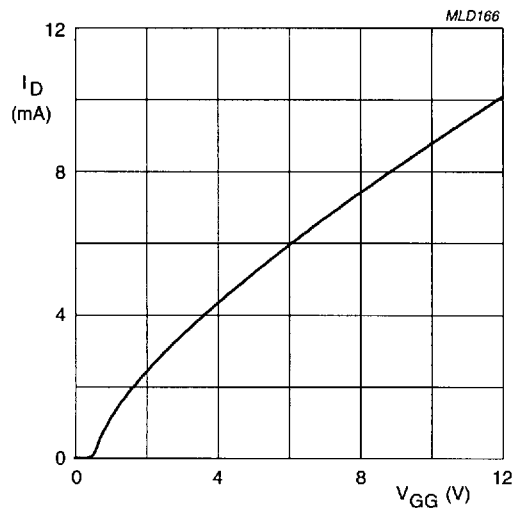
$V_{G2\text{-}S}$ = 4 V.
R_{G1} connected to V_{GG}.
T_j = 25 °C.

Fig.11 Drain current as a function of gate 1 supply voltage (= V_{GG}) and drain supply voltage; typical values; see Fig.26.



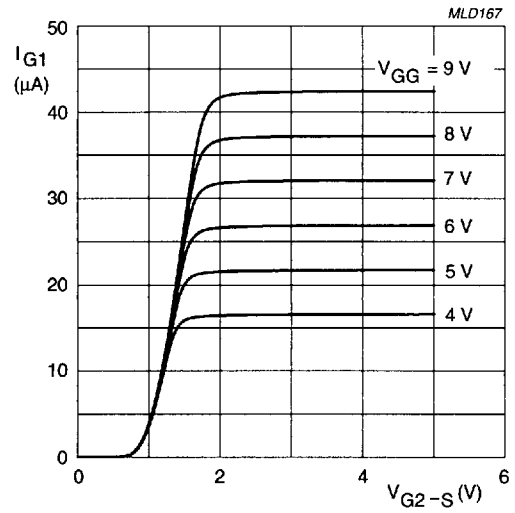
V_{DS} = 9 V; $V_{G2\text{-}S}$ = 4 V.
R_{G1} = 180 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.12 Drain current as a function of gate 1 voltage (= V_{GG}); typical values; see Fig.26.



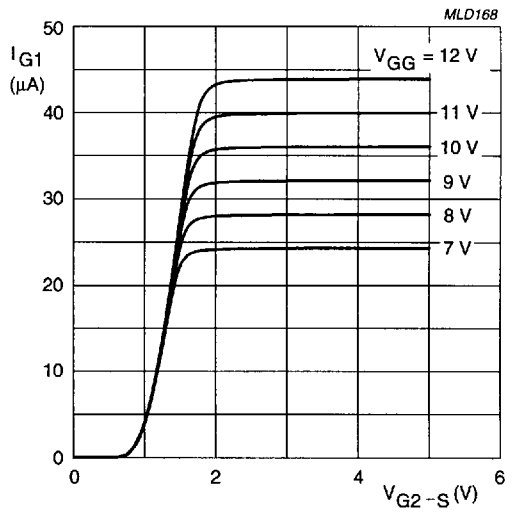
V_{DS} = 12 V; $V_{G2\text{-}S}$ = 4 V.
R_{G1} = 250 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.13 Drain current as a function of gate 1 voltage (= V_{GG}); typical values; see Fig.26.



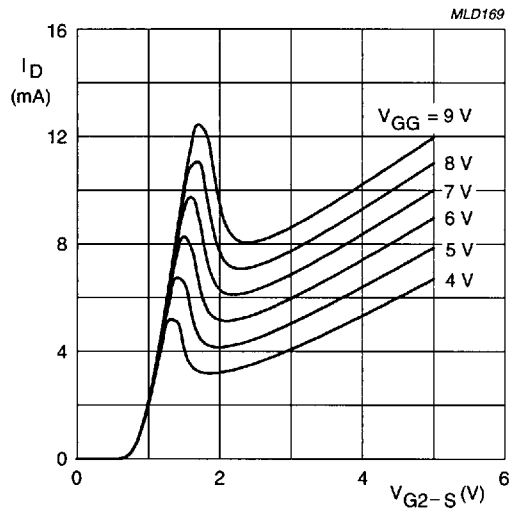
V_{DS} = 9 V.
R_{G1} = 180 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.14 Gate 1 current as a function of gate 2 voltage; typical values.



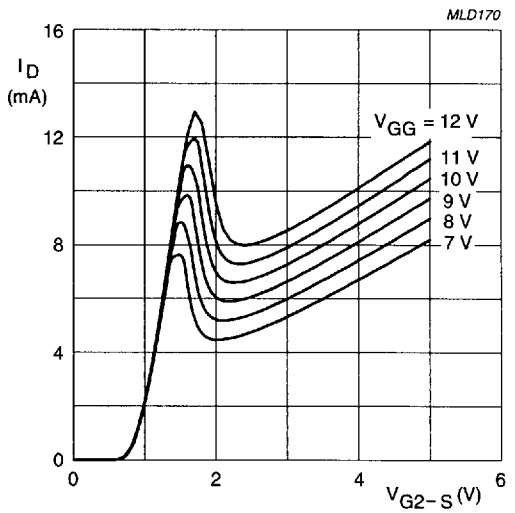
V_{DS} = 12 V.
R_{G1} = 250 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.15 Gate 1 current as a function of gate 2 voltage; typical values.



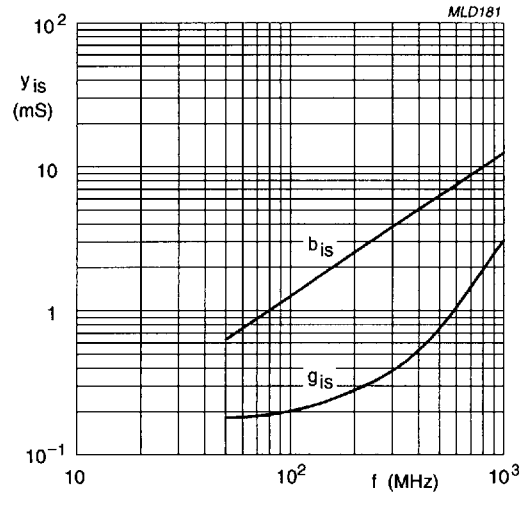
V_{DS} = 9 V.
R_{G1} = 180 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.16 Drain current as a function of the gate 2 voltage; typical values; see Fig.26.



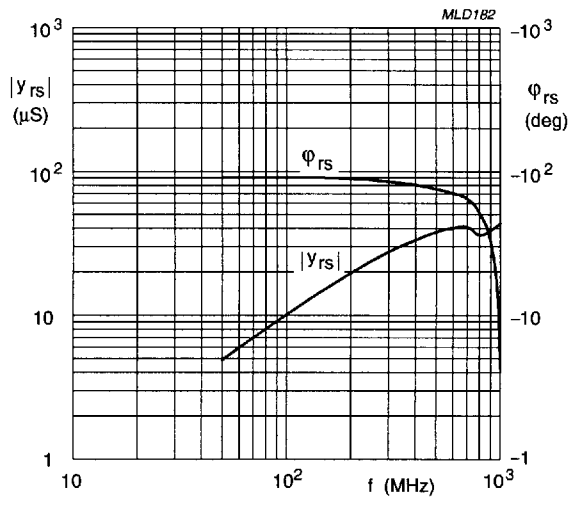
V_{DS} = 12 V.
R_{G1} = 250 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.17 Drain current as a function of the gate 2 voltage; typical values; see Fig.26.



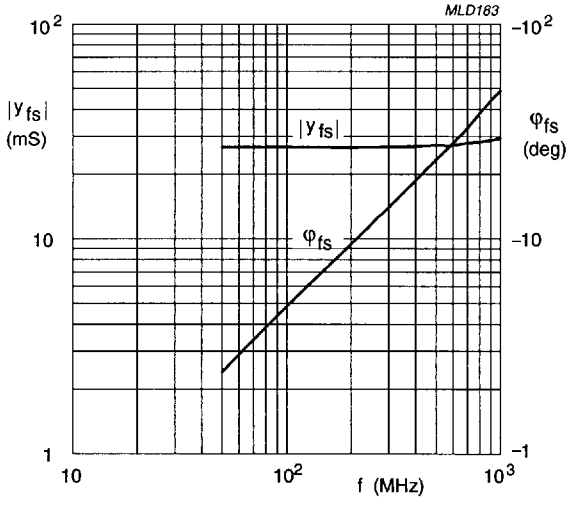
V_{DS} = 9 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.18 Input admittance as a function of frequency; typical values.



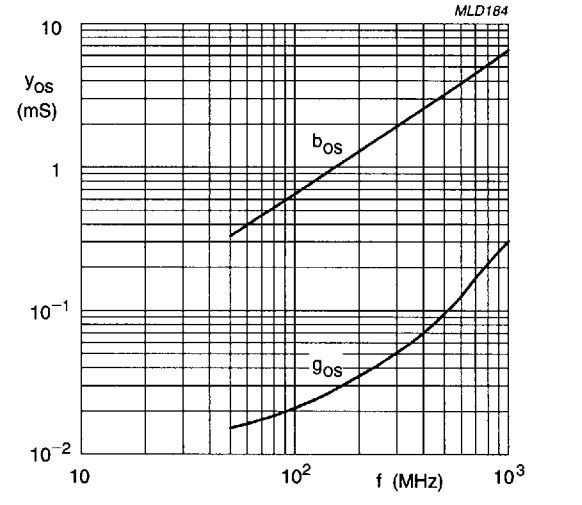
V_{DS} = 9 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.19 Reverse transfer admittance and phase as a function of frequency; typical values.



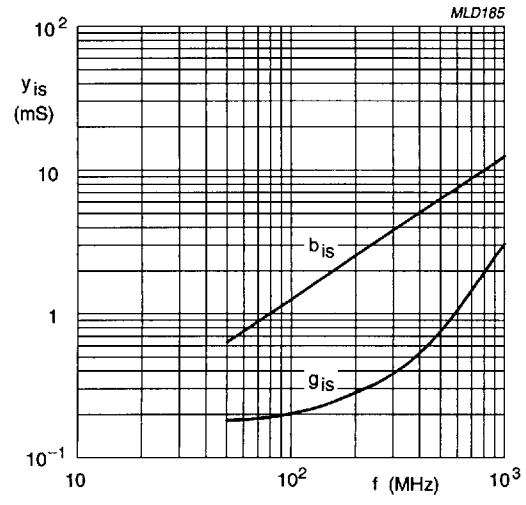
V_{DS} = 9 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.20 Forward transfer admittance and phase as a function of frequency; typical values.



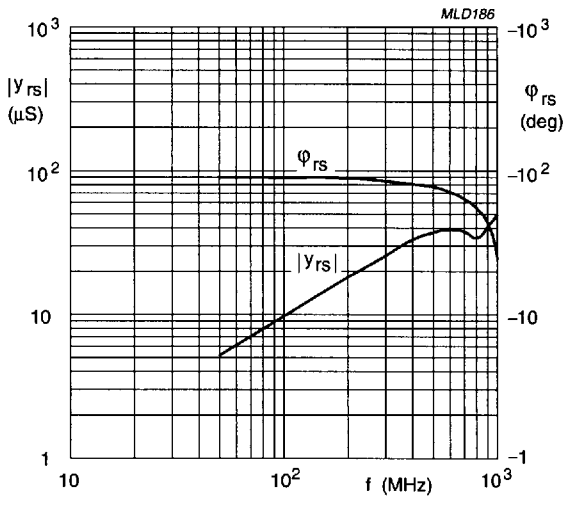
V_{DS} = 9 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.21 Output admittance as a function of frequency; typical values.



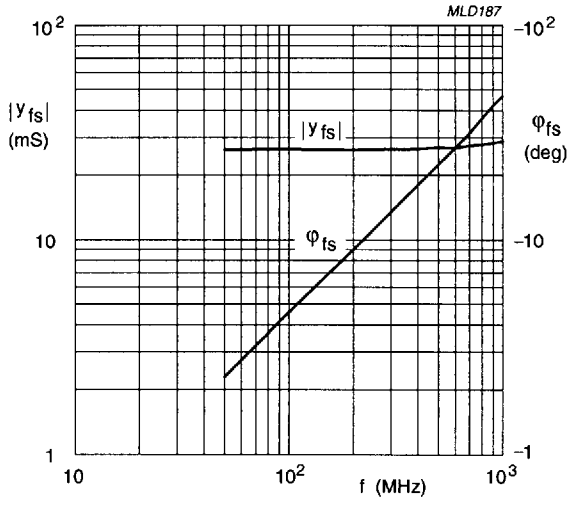
V_{DS} = 12 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.22 Input admittance as a function of frequency; typical values.



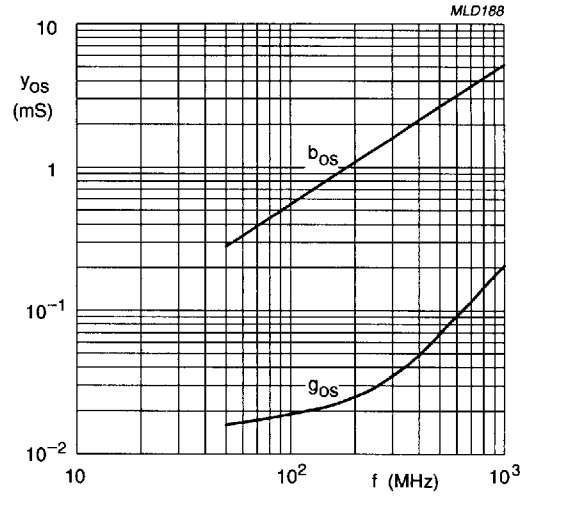
V_{DS} = 12 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.23 Reverse transfer admittance and phase as a function of frequency; typical values.



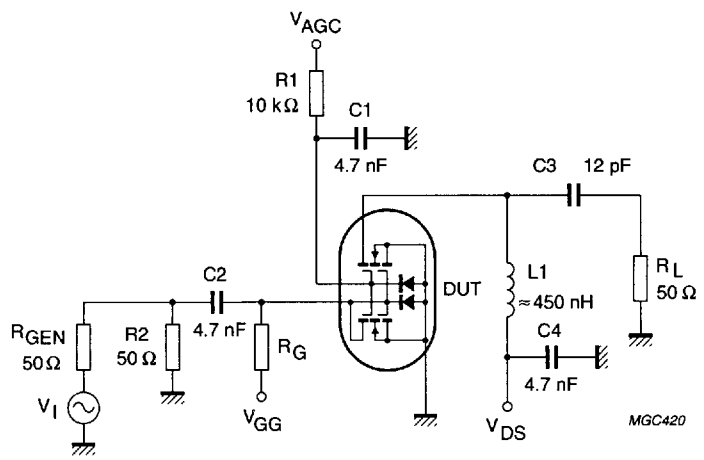
V_{DS} = 12 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.24 Forward transfer admittance and phase as a function of frequency; typical values.



V_{DS} = 12 V; V_{G2} = 4 V.
I_D = 10 mA; T_{amb} = 25 °C.

Fig.25 Output admittance as a function of frequency; typical values.



For $V_{GG} = V_{DS} = 9$ V, $R_G = 180$ kΩ.
For $V_{GG} = V_{DS} = 12$ V, $R_G = 250$ kΩ.

Fig.26 Cross-modulation test circuit.

Table 1 Scattering parameters: V_{DS} = 9 V; $V_{G2\text{-}S}$ = 4 V; I_D = 10 mA

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.985	−3.9	2.618	175.1	0.001	137.9	1.000	−1.9
100	0.981	−7.3	2.602	170.5	0.001	80.4	0.999	−4.0
200	0.975	−14.4	2.577	160.7	0.002	74.0	0.995	−7.6
300	0.965	−21.6	2.555	151.6	0.002	79.3	0.994	−11.3
400	0.947	−28.3	2.513	141.8	0.003	80.5	0.992	−15.0
500	0.927	−34.9	2.449	133.4	0.003	82.8	0.988	−18.5
600	0.913	−41.7	2.339	124.6	0.003	78.9	0.984	−22.0
700	0.890	−47.9	2.361	115.4	0.003	80.6	0.982	−25.3
800	0.869	−54.0	2.302	106.4	0.003	93.9	0.979	−28.8
900	0.845	−59.7	2.228	97.6	0.003	104.8	0.976	−32.1
1000	0.823	−65.4	2.167	89.6	0.003	129.3	0.974	−35.5

Table 2 Noise data: V_{DS} = 9 V; $V_{G2\text{-}S}$ = 4 V; I_D = 10 mA

f (MHz)	F_{min} (dB)	Γ_{opt}		r_n
		(ratio)	(deg)	
800	2.00	0.67	43.9	0.89

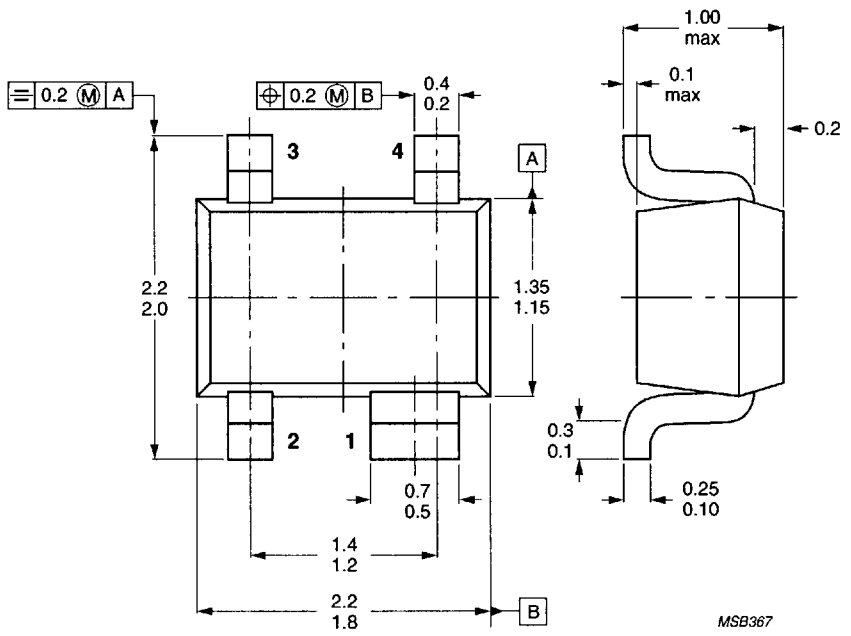
Table 3 Scattering parameters: V_{DS} = 12 V; $V_{G2\text{-}S}$ = 4 V; I_D = 10 mA

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.985	−3.7	2.576	175.3	0.000	125.0	1.000	−1.6
100	0.980	−7.4	2.563	170.9	0.001	111.2	1.000	−3.3
200	0.973	−14.6	2.541	161.6	0.002	83.0	0.997	−6.4
300	0.962	−21.5	2.519	152.9	0.002	85.2	0.996	−9.3
400	0.946	−28.5	2.479	143.5	0.003	79.4	0.995	−12.4
500	0.929	−35.0	2.419	135.5	0.003	78.2	0.991	−15.3
600	0.912	−41.6	2.373	127.2	0.003	80.0	0.989	−18.1
700	0.895	−47.8	2.336	118.7	0.003	83.4	0.987	−20.9
800	0.868	−53.8	2.284	110.0	0.003	91.3	0.985	−23.7
900	0.845	−59.8	2.213	101.6	0.003	95.9	0.983	−26.5
1000	0.823	−65.7	2.160	94.1	0.003	112.2	0.981	−29.3

Table 4 Noise data: V_{DS} = 12 V; $V_{G2\text{-}S}$ = 4 V; I_D = 10 mA

f (MHz)	F_{min} (dB)	Γ_{opt}		r_n
		(ratio)	(deg)	
800	2.00	0.66	43.3	0.97

PACKAGE OUTLINE



Dimensions in mm.

Fig.27 SOT343R.